

**This Page Is Inserted by IFW Operations
and is not a part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- **BLACK BORDERS**
- **TEXT CUT OFF AT TOP, BOTTOM OR SIDES**
- **FADED TEXT**
- **ILLEGIBLE TEXT**
- **SKEWED/SLANTED IMAGES**
- **COLORED PHOTOS**
- **BLACK OR VERY BLACK AND WHITE DARK PHOTOS**
- **GRAY SCALE DOCUMENTS**

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

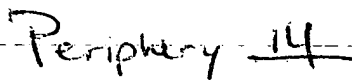


Figure 1
Prior Art

TOP SECRET

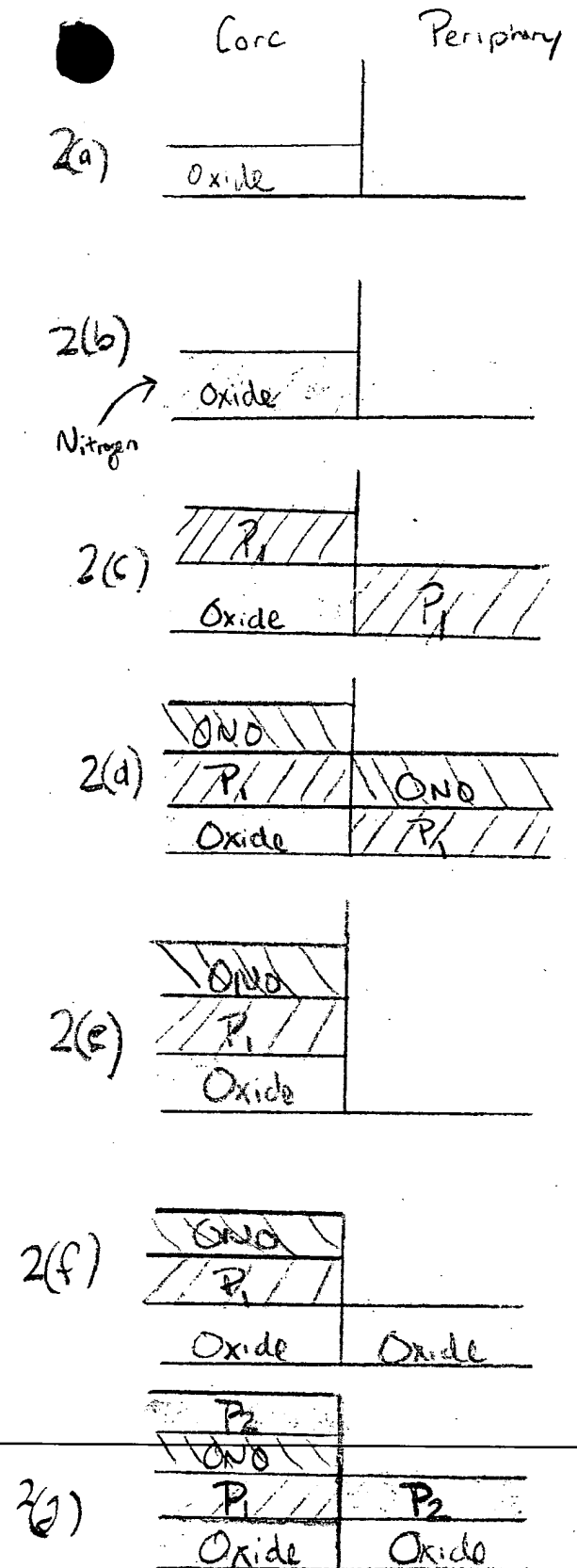
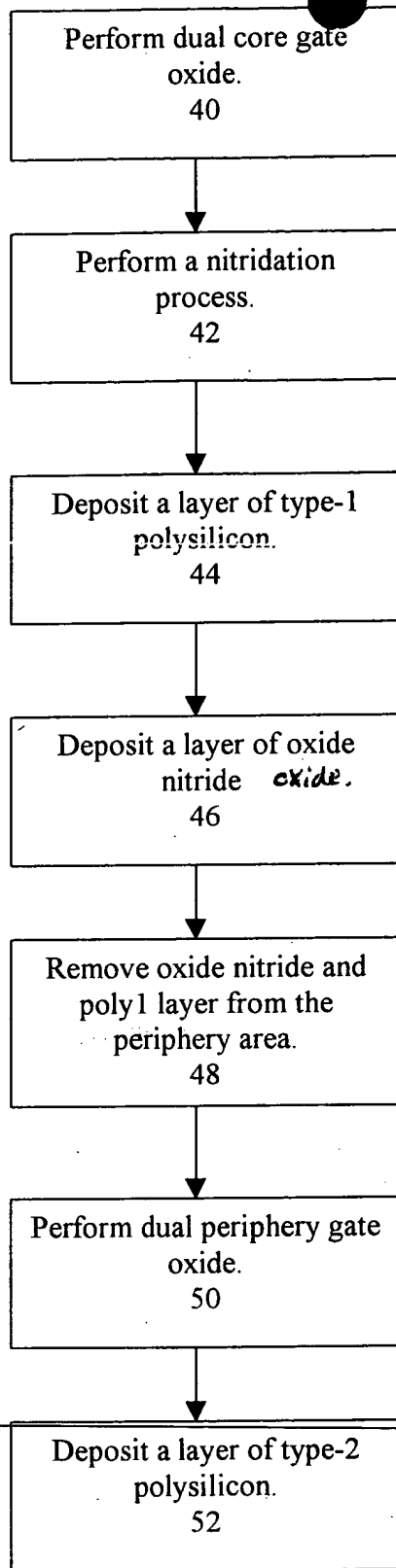


FIGURE 2
PRIOR ART


```
graph TD; 200[Provide a portion of the dual periphery gate oxide. 200] --> 202[Provide a dual core gate oxide and complete the dual periphery gate oxide. 202]; 202 --> 204[Provide a nitridation process. 204]; 204 --> 206[Deposit a layer of type-1 polysilicon. 206]; 206 --> 208[Deposit a layer of oxide nitride. 208]; 208 --> 210[Remove oxide nitride and a portion of the poly1 layer from the periphery area. 210]; 210 --> 212[Deposit a layer of type-2 polysilicon. 212];
```

Provide a portion of the dual periphery gate oxide.
200

Provide a dual core gate oxide and complete the dual periphery gate oxide.
202

Provide a nitridation process.
204

Deposit a layer of type-1 polysilicon.
206

Deposit a layer of oxide nitride.
208

Remove oxide nitride and a portion of the poly1 layer from the periphery area.
210

Deposit a layer of type-2 polysilicon.
212

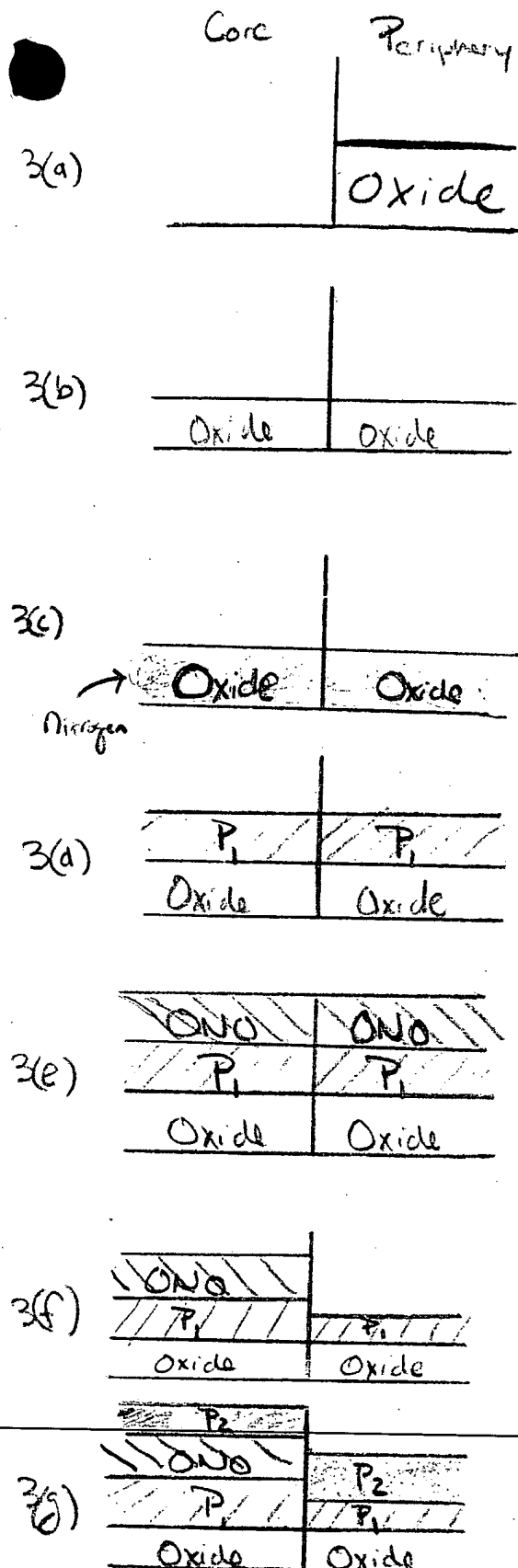


FIGURE 3

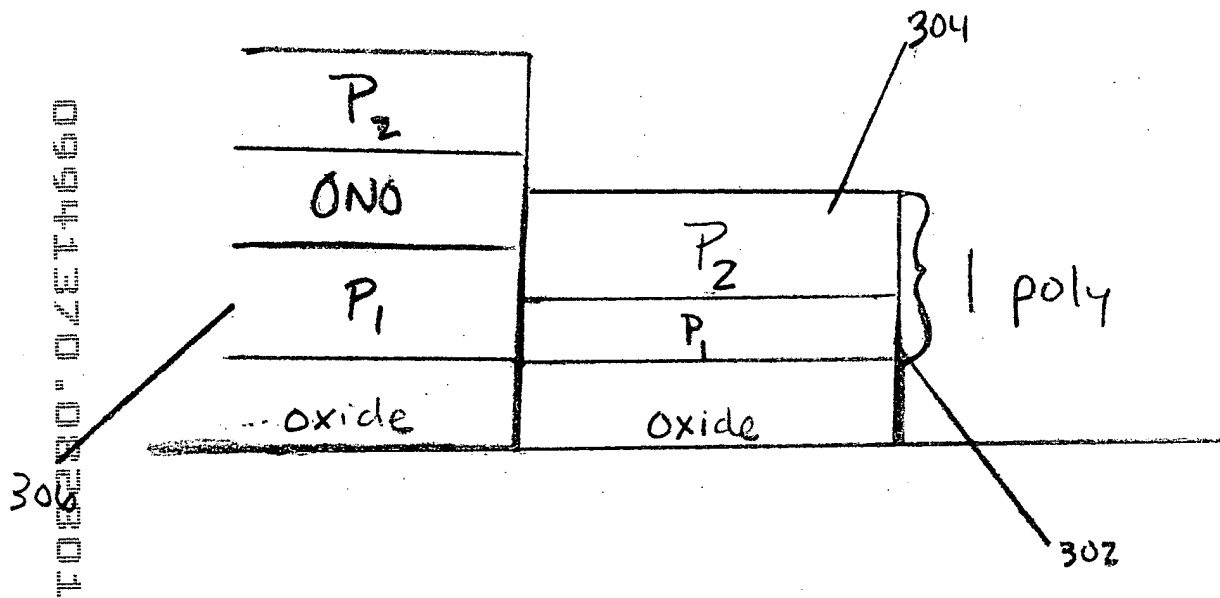


Figure 4